SPECIFICATION AMENDMENTS

Replace the paragraph beginning at page 1, line 6 with:

The present invention relates to an apparatus ~~of~~ for manufacturing a semiconductor device, and specifically relates to a wet-etching apparatus provided with ultraviolet-light radiation apparatus, a wet-etching method, and a method of manufacturing a semiconductor device.

Replace the paragraph beginning at page 1, line 14 with:

Background art, not prior art, includes a wet-etching method wherein, after a chemical solution is ~~coated on~~ applied to a film to be processed on a substrate, ultraviolet light ~~is radiated to~~ irradiates the film through the chemical solution to break the molecular bonds of the film, as described in Japanese Patent Application No. 2003-21566 (Fig. 1).

Replace the paragraph beginning at page 1, line 27 with:

If the contact angle between the chemical solution and the film is large, as described above, the coating of the chemical solution 31 is ~~thickly coated~~ thick as Fig. 5 shows. In a wet-etching method wherein ultraviolet light ~~is radiated on~~ irradiates the film on the substrate 5 through the chemical solution 20, the ~~thickly coated~~ thick chemical solution 31 interferes with the transmission of the ultraviolet light, and the light energy of the ultraviolet light is attenuated in the chemical solution 31. Therefore, there has been a problem that the effect ~~to break~~ of breaking the molecular bonds of the film to be processed is weakened, and the desired etching rate cannot be achieved.

Replace the paragraph beginning at page 2, line 5 with:

In wet etching by radiating ultraviolet light in ~~the atmosphere~~ an ambient containing oxygen, if ultraviolet light of a wavelength having a high absorption coefficient ~~to~~ in oxygen is used, the light energy of the ultraviolet light is attenuated before the ultraviolet light reaches the film to be processed. In this case also, the effect ~~to break~~ of breaking the molecular ~~bond~~ bonds of the film to be processed is weakened, leading to the loss of light energy. In order to solve such a problem, there is a method for ~~performing~~ wet etching in ~~the state filled with~~ an inert gas, such as nitrogen (N_2), to lower the oxygen content to a

predetermined value or below. However, to realize this method, there has been a problem of increased equipment costs because of the necessity to provide the etching apparatus with a sealing mechanism 32 as Fig. 6 shows, and increased operation costs due to the wasteful consumption of the inert gas. Also since the displacement of atmosphere in the sealing mechanism 32 is necessary, there has been a problem of requiring a long treatment time, and a lowered throughput.

Replace the paragraph beginning at page 4, line 14 with:

Fig. 3 is a view ~~for~~ illustrating ~~the case that~~ a thin coating of a chemical solution ~~is thinly coated~~ on a film to be etched, on a substrate;

Replace the paragraph beginning at page 4, line 21 with:

Fig. 5 is a view ~~for~~ illustrating ~~the case that~~ a thick coating of a chemical solution ~~is thickly coated~~ on a film to be etched, on a substrate; and